L Number	Hits	Search Text	DB	Time stamp
1	83	(((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT;	2004/10/27 17:24
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) and	US-PGPUB;	
		(silicide or salicide or polycide or policide )).ab.) and (@ad <	EPO; JPO;	
		"20020724")	DERWENT;	
			IBM_TDB	
2	67	'''	USPAT;	2004/10/27 17:22
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) and	US-PGPUB;	
		(silicide or salicide or polycide or policide )).ab.) and (@ad <	EPO; JPO;	
		"20010724")	DERWENT;	
2	16	////transh nagro //magfat an /matal adi avida adi asmisandusas	IBM_TDB	0004/40/07 47:00
3	16	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet ) or gate))	USPAT; US-PGPUB;	2004/10/27 17:23
		and (silicide or salicide or polycide or policide )).ab.) and (@ad <	EPO; JPO;	
		"20020724")) not ((((trench near2 ((mosfet or (metal adj oxide adj	DERWENT;	
		semiconducor adj (fet or field)) or pmos or cmos or nmos or	IBM_TDB	
		misfet ) or gate)) and (silicide or salicide or polycide or policide	15.11_155	
		)).ab.) and (@ad < "20010724") )		
4	164	(((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT;	2004/10/27 17:25
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) same	US-PGPUB;	
		(silicide or salicide or polycide or policide ))) and (@ad <	EPO; JPO;	
		"20010724")	DERWENT;	
•			IBM_TDB	
5	209	(((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT;	2004/10/27 17:25
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) same	US-PGPUB;	
		(silicide or salicide or polycide or policide ))) and (@ad <	EPO; JPO;	
	ļ	"20020724")	DERWENT;	
6	146	((((transh near) ((maefet or (metal adi evide adi comiconducer	IBM_TDB	2004/10/27 18:17
O	140	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet ) or gate))	USPAT; US-PGPUB;	2004/10/27 16:17
		same (silicide or salicide or polycide or policide ))) and (@ad <	EPO; JPO;	
		"20020724")) not ((((trench near2 ((mosfet or (metal adj oxide adj	DERWENT;	
		semiconducor adj (fet or field)) or pmos or cmos or nmos or	IBM_TDB	
		misfet ) or gate)) and (silicide or salicide or polycide or policide	.5	
		)).ab.) and (@ad < "20020724"))		
7	. 8	"6312993" `	USPAT;	2004/10/27 18:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		· · · · · · · · · · · · · · · · · · ·	IBM_TDB	
8	3	(("6312993") or ("6215149") or ("6097061")).PN.	USPAT	2004/10/27 18:18
9 10	2 3	("6025237"   "6114065").PN.	USPAT USPAT	2004/10/27 18:18
11	8	6312993.URPN.   ("5710438"   "5777370"   "5937315"   "5955770"   "5962904"	USPAT	2004/10/27 18:18 2004/10/27 18:19
• •	•	(3710438   3777370   5937315   5955770   5962904     "5990528"   "6025620"   "6054744").PN.	JOSEAN	2004/10/2/ 10.19
12	5	6215149.URPN.	USPAT	2004/10/27 18:20
13	7	("5016067"   "5378655"   "5705415"   "5770878"   "5773343"	USPAT	2004/10/27 18:20
_	1	"5883399"   "5953602").PN.		= 30 10.27
14	6	6097061.URPN.	USPAT	2004/10/27 18:21
15	2797		USPAT;	2004/10/27 18:27
			US-PGPUB;	
		į	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1 1	6707100.pn.	USPAT	2004/10/26 13:42
-	24	(("6479357") or ("6489204") or ("6509608") or ("6534367") or	USPAT;	2004/10/27 15:15
		("6465866") or ("6413822") or ("6476444") or ("6586800") or	US-PGPUB;	
		("6252277") or ("6251730") or ("6051468") or ("5753554")).PN.	EPO; JPO;	
			DERWENT;   IBM_TDB	
	198671	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or	USPAT;	2004/10/27 15:43
	1,300,1	pmos or cmos or nmos or misfet	US-PGPUB;	2004/10/2/ 13.43
	!	Prince of alliage of fillings of fillings	EPO; JPO;	
	i	•	DERWENT;	
•	1		I DEIXAGENT.	

-	5850	trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT;	2004/10/27 15:43
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	63833	silicide or salicide or polycide or policide	USPAT;	2004/10/27 15:43
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	00	//branch	IBM_TDB	0004/40/07 45 44
-	98	((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT;	2004/10/27 15:44
		(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) and	US-PGPUB;	
		(silicide or salicide or polycide or policide )).ab.	EPO; JPO; DERWENT:	
			IBM TDB	
_	67	(((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj	USPAT:	2004/10/27 17:22
	1	(fet or field)) or pmos or cmos or nmos or misfet ) or gate)) and	US-PGPUB;	2007/10/21 17.22
		(silicide or salicide or polycide or policide )).ab.) and (@ad <	EPO; JPO;	
		"20010724")	DERWENT;	
			IBM TDB	